® **Integrated Device Technology, Inc.**

HIGH-SPEED
1K x 8 FourPort™
STATIC RAM

FEATURES:

• High-speed access
— Military: 30/35/45ns (max.)
— Commercial: 25/30/35/45ns (max.)
• Low-power operation
— IDT7050S
Active: 750mW (typ.)
Standby: 10mW (typ.)
— IDT7050L
Active: 750mW (typ.)
Standby: 1.5mW (typ.)
• Fully asynchronous operation from each of the four ports: P1, P2, P3, P4
• Versatile control for write-inhibit: separate $\overline{BUSY}$ input to control write-inhibit for each of the four ports
• Battery backup operation—2V data retention
• TTL-compatible; single 5V (±10%) power supply
• Available in several popular hermetic and plastic packages for both through-hole and surface mount
• Military product compliant to MIL-STD-883, Class B
• Industrial temperature range (-40°C to +85°C) is available, tested to military electrical sspecification

DESCRIPTION:

The IDT7050 is a high-speed 1K x 8 FourPort static RAM designed to be used in systems where multiple access into a common RAM is required. This FourPort static RAM offers increased system performance in multiprocessor systems that have a need to communicate in real time and also offers added benefit for high-speed systems in which multiple access is required in the same cycle.
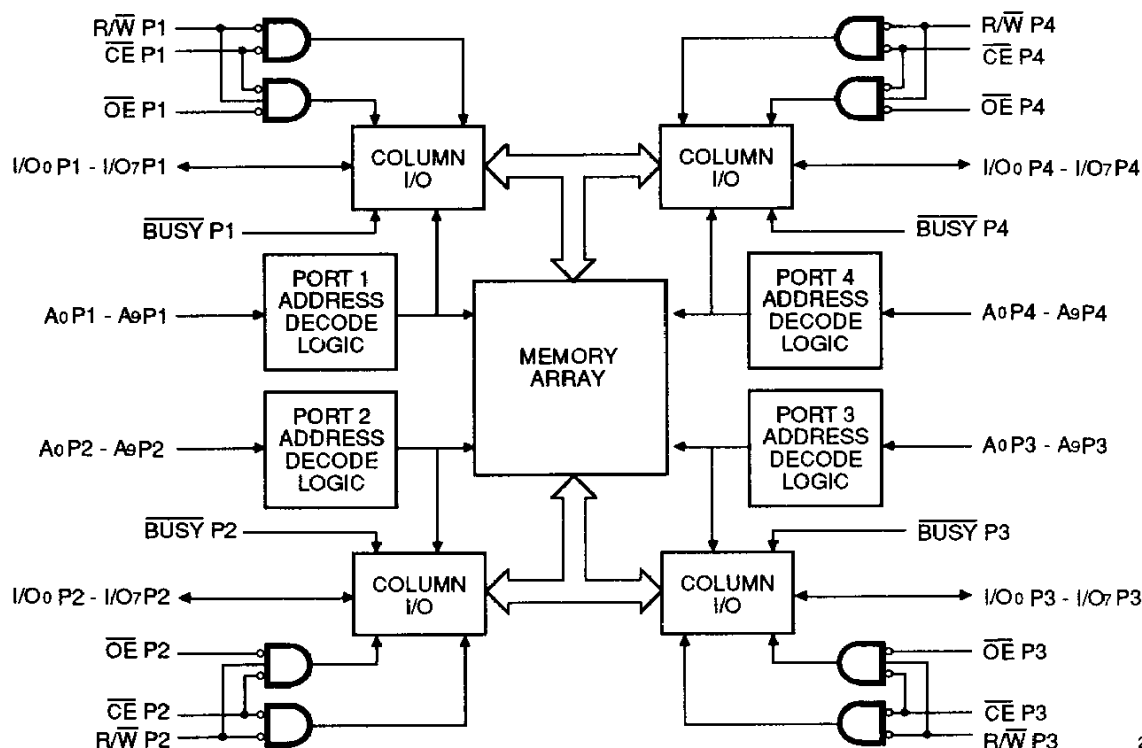
The IDT7050 is also designed to be used in systems where on-chip hardware port arbitration is not needed. This part lends itself to those systems which cannot tolerate wait states or are designed to be able to externally arbitrate or withstand contention when all ports simultaneously access the same FourPort RAM location.

The IDT7050 provides four independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. It is the user's responsibility to ensure data integrity when simultaneously accessing the same memory location from all ports. An automatic power down feature, controlled by $\overline{CE}$, permits the on-chip circuitry of each port to enter a very low power standby power mode.

Fabricated using IDT's CEMOS™ high-performance technology, this four port RAM typically operates on only 750mW of power at maximum access times as fast as 25ns. Low-power (L) versions offer battery backup data retention capability, with each port typically consuming 50μW from a 2V battery.

The IDT7050 is packaged in a ceramic 108-pin PGA and a plastic 132-pin quad flatpack. Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B.

FUNCTIONAL BLOCK DIAGRAM

FourPort is a trademark of Integrated Device Technology, Inc.

2698 drw 01

MILITARY AND COMMERCIAL TEMPERATURE RANGES   **APRIL 1992**

	A	B	C	D	E	F	G	H	J	K	L	M	
	81 $R/\overline{W}$ P2	80 NC	77 A_7 P2	74 A_5 P2	72 A_3 P2	69 A_0 P2	68 A_0 P3	65 A_3 P3	63 A_5 P3	60 A_7 P3	57 NC	54 $R/\overline{W}$ P3	12
	84 $\overline{BUSY}$ P2	83 $\overline{OE}$ P2	78 A_8 P2	76 NC	73 A_4 P2	70 A_1 P2	67 A_1 P3	64 A_4 P3	61 NC	59 A_8 P3	56 $\overline{OE}$ P3	53 $\overline{BUSY}$ P3	11
	87 A_2 P1	86 A_1 P1	82 $\overline{CE}$ P2	79 A_9 P2	75 A_6 P2	71 A_2 P2	66 A_2 P3	62 A_6 P3	58 A_9 P3	55 $\overline{CE}$ P3	51 A_1 P4	50 A_2 P4	10
	90 A_5 P1	88 A_3 P1	85 A_0 P1							52 A_0 P4	49 A_3 P4	47 A_5 P4	09
	92 NC	91 A_6 P1	89 A_4 P1							48 A_4 P4	46 A_6 P4	45 NC	08
	95 A_8 P1	94 A_7 P1	93 Vcc							44 GND	43 A_7 P4	42 A_8 P4	07
	96 A_9 P1	97 NC	98 $\overline{CE}$ P1							39 $\overline{CE}$ P4	40 NC	41 A_9 P4	06
	99 $R/\overline{W}$ P1	100 $\overline{OE}$ P1	102 I/O_0 P1							35 GND	37 $\overline{OE}$ P4	38 $R/\overline{W}$ P4	05
	101 $\overline{BUSY}$ P1	103 I/O_1 P1	106 GND							31 GND	34 I/O_7 P4	36 $\overline{BUSY}$ P4	04
	104 I/O_2 P1	105 I/O_3 P1	1 I/O_6 P1	4 Vcc	8 GND	12 Vcc	17 Vcc	21 GND	25 Vcc	28 I/O_2 P4	32 I/O_5 P4	33 I/O_6 P4	03
	107 I/O_4 P1	2 I/O_7 P1	5 I/O_0 P2	7 I/O_2 P2	10 I/O_4 P2	13 I/O_6 P2	16 I/O_1 P3	19 I/O_3 P3	22 I/O_5 P3	24 I/O_7 P3	29 I/O_3 P4	30 I/O_4 P4	02
	108 I/O_5 P1	3 NC	6 I/O_1 P2	9 I/O_3 P2	11 I/O_5 P2	14 I/O_7 P2	15 I/O_0 P3	18 I/O_2 P3	20 I/O_4 P3	23 I/O_6 P3	26 I/O_0 P4	27 I/O_1 P4	01
	A	B	C	D	E	F	G	H	J	K	L	M	

Center of diagram:
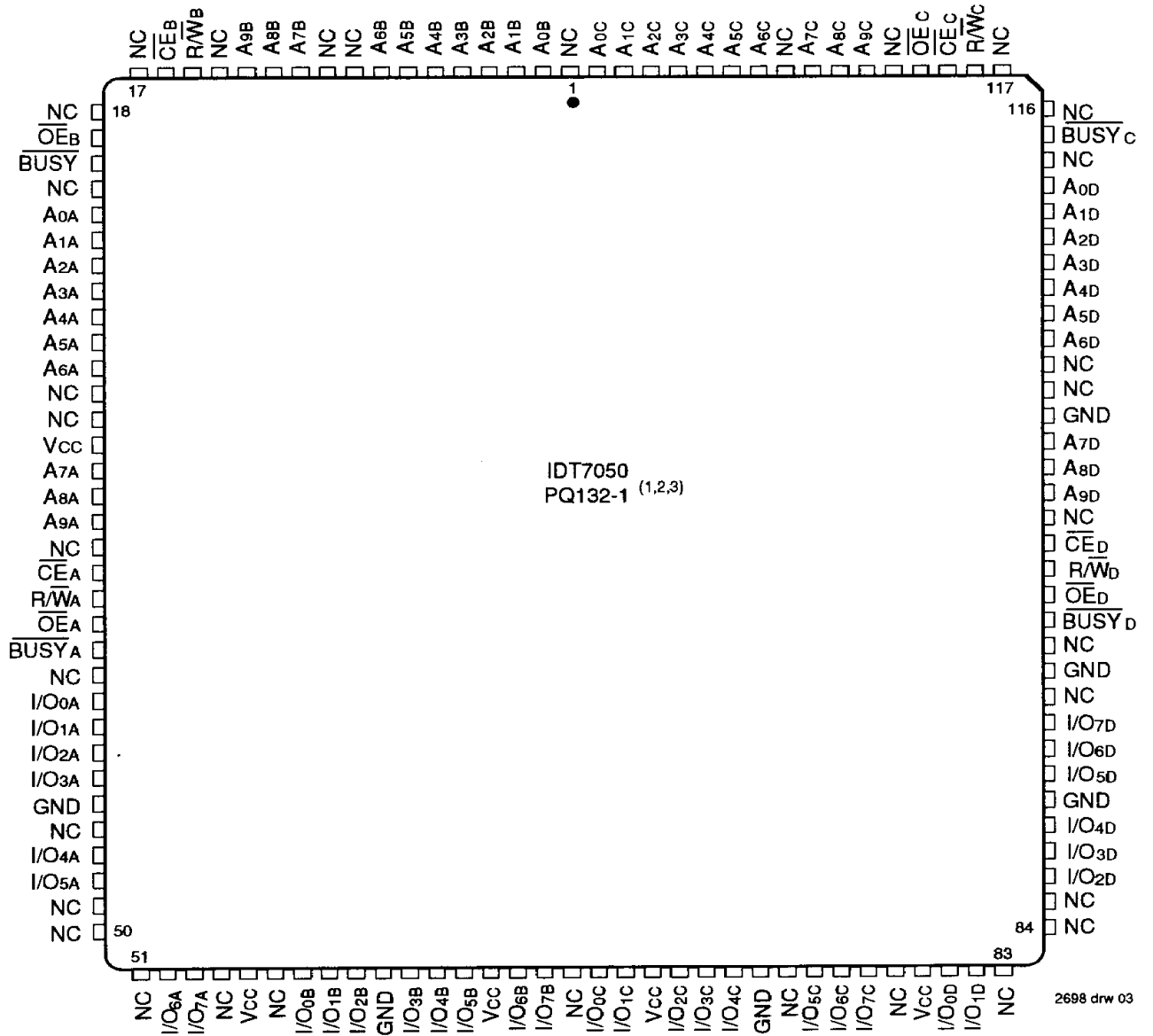
IDT7050
G108-1 [1,2,3]

TOP VIEW

2698 drw 02

Pin 1
Designator

NOTES:
1. All Vcc pins must be connected to the power supply.
2. All GND pins must be connected to the ground supply.
3. NC denotes no - connect pin.

6

Top pins (left to right): NC, $\overline{CE}_B$, $R/\overline{W}_B$, NC, A9B, A8B, A7B, NC, NC, A6B, A5B, A4B, A3B, A2B, A1B, A0B, NC, A0C, A1C, A2C, A3C, A4C, A5C, A6C, NC, A7C, A8C, A9C, NC, $\overline{OE}_C$, $\overline{CE}_C$, $R/\overline{W}_C$, NC

Left pins (top to bottom): NC, $\overline{OE}_B$, BUSY, NC, A0A, A1A, A2A, A3A, A4A, A5A, A6A, NC, NC, Vcc, A7A, A8A, A9A, NC, $\overline{CE}_A$, $R/\overline{W}_A$, $\overline{OE}_A$, BUSY_A, NC, I/O0A, I/O1A, I/O2A, I/O3A, GND, NC, I/O4A, I/O5A, NC, NC

Right pins (top to bottom): NC, BUSY_C, NC, A0D, A1D, A2D, A3D, A4D, A5D, A6D, NC, NC, GND, A7D, A8D, A9D, NC, $\overline{CE}_D$, $R/\overline{W}_D$, $\overline{OE}_D$, BUSY_D, NC, GND, NC, I/O7D, I/O6D, I/O5D, GND, I/O4D, I/O3D, I/O2D, NC, NC

Bottom pins (left to right): NC, I/O6A, I/O7A, NC, VCC, NC, I/O0B, I/O1B, I/O2B, GND, I/O3B, I/O4B, I/O5B, VCC, I/O6B, I/O7B, NC, I/O0C, I/O1C, VCC, I/O2C, I/O3C, I/O4C, GND, NC, I/O5C, I/O6C, I/O7C, NC, VCC, I/O0D, I/O1D, NC

Center label:
IDT7050
PQ132-1 [1,2,3]

Corner numbers: 17, 18, 1, 117, 116, 50, 51, 84, 83

2698 drw 03

NOTES:
1. All Vcc pins must be connected to the power supply.
2. All GND pins must be connected to the ground supply.
3. NC denotes no - connect pin.

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PIN CONFIGURATIONS

Symbol	Pin Name
A_0 P1 – A_9 P1	Address Lines – Port 1
A_0 P2 – A_9 P2	Address Lines – Port 2
A_0 P3 – A_9 P3	Address Lines – Port 3
A_0 P4 – A_9 P4	Address Lines – Port 4
I/O$_0$ P1 – I/O$_7$ P1	Data I/O – Port 1
I/O$_0$ P2 – I/O$_7$ P2	Data I/O – Port 2
I/O$_0$ P3 – I/O$_7$ P3	Data I/O – Port 3
I/O$_0$ P4 – I/O$_7$ P4	Data I/O – Port 4
R/$\overline{W}$ P1	Read/Write – Port 1
R/$\overline{W}$ P2	Read/Write – Port 2
R/$\overline{W}$ P3	Read/Write – Port 3
R/$\overline{W}$ P4	Read/Write – Port 4
GND	Ground
$\overline{CE}$ P1	Chip Enable – Port 1
$\overline{CE}$ P2	Chip Enable – Port 2
$\overline{CE}$ P3	Chip Enable – Port 3
$\overline{CE}$ P4	Chip Enable – Port 4
$\overline{OE}$ P1	Output Enable – Port 1
$\overline{OE}$ P2	Output Enable – Port 2
$\overline{OE}$ P3	Output Enable – Port 3
$\overline{OE}$ P4	Output Enable – Port 4
$\overline{BUSY}$ P1	Write Disable – Port 1
$\overline{BUSY}$ P2	Write Disable – Port 2
$\overline{BUSY}$ P3	Write Disable – Port 3
$\overline{BUSY}$ P4	Write Disable – Port 4
Vcc	Power

2698 tbl 01

ABSOLUTE MAXIMUM RATINGS[1]

Symbol	Rating	Commercial	Military	Unit
VTERM[2]	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
IOUT	DC Output Current	50	50	mA

NOTE: 2698 tbl 02
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. VTERM must not exceed Vcc + 0.5V.

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter[1]	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 0V	11	pF
COUT	Output Capacitance	VOUT = 0V	11	pF

NOTE: 2698 tbl 03
1. This parameter is determined by device characterization but is not production tested.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

2698 tbl 04

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
VIH	Input High Voltage	2.2	—	6.0[2]	V
VIL	Input Low Voltage	-0.5[1]	—	0.8	V

NOTE: 2698 tbl 05
1. VIL (min.) = -3.0V for pulse width less than 20ns.
2. VTERM must not exceed Vcc + 0.5V.

6

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DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE (Vcc = 5.0V ± 10%)

Symbol	Parameter	Test Conditions	IDT7050S Min.	IDT7050S Max.	IDT7050L Min.	IDT7050L Max.	Unit
$|I_{LI}|$	Input Leakage Current[7]	V_{CC} = 5.5V, V_{IN} = 0V to V_{CC}	—	10	—	5	µA
$|I_{LO}|$	Output Leakage Current	$\overline{CE}$ = V_{IH}, V_{OUT} = 0V to V_{CC}	—	10	—	5	µA
V_{OL}	Output Low Voltage	I_{OL} = 4mA	—	0.4	—	0.4	V
V_{OH}	Output High Voltage	I_{OH} = -4mA	2.4	—	2.4	—	V

2698 tbl 06

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE[1, 2, 6] (Vcc = 5.0V ± 10%)

Symbol	Parameter	Test Condition	Version		IDT7050x25[3] Typ.	Max.	IDT7050x30 Typ.	Max.	IDT7050x35 Typ.	Max.	IDT7050x45 Typ.	Max.	Unit
I_{CC1}	Operating Power Supply Current (All Ports Active)	$\overline{CE} \leq V_{IL}$ Outputs Open f = 0[4]	MIL.	S	—	—	150	360	150	360	150	360	mA
				L	—	—	150	300	150	300	150	300	
			COM'L.	S	150	300	150	300	150	300	150	300	
				L	150	250	150	250	150	250	150	250	
I_{CC2}	Dynamic Operating Current (All Ports Active)	$\overline{CE} \leq V_{IL}$ Outputs Open f = f_{MAX}[5]	MIL.	S	—	—	220	400	210	395	195	390	mA
				L	—	—	190	335	180	330	170	325	
			COM'L.	S	225	350	220	340	210	335	195	330	
				L	195	305	190	295	180	290	170	285	
I_{SB}	Standby Current (All Ports — TTL Level Inputs)	$\overline{CE} \geq V_{IH}$ f = f_{MAX}[5]	MIL.	S	—	—	45	115	40	110	35	105	mA
				L	—	—	40	85	35	80	30	75	
			COM'L.	S	60	85	45	80	40	75	35	70	
				L	50	70	40	65	35	60	30	55	
I_{SB1}	Full Standby Current (All Ports — All CMOS Level Inputs)	All Ports $\overline{CE} \geq V_{CC}$ - 0.2V, $V_{IN} \geq V_{CC}$ - 0.2V or $V_{IN} \leq 0.2V$, f = 0[4]	MIL.	S	—	—	1.5	30	1.5	30	1.5	30	mA
				L	—	—	.3	4.5	.3	4.5	.3	4.5	
			COM'L.	S	1.5	15	1.5	15	1.5	15	1.5	15	
				L	.3	1.5	.3	1.5	.3	1.5	.3	1.5	

2698 tbl 07

NOTES:
1. "x" in part number indicates power rating (S or L).
2. V_{CC} = 5V, T_A = +25°C for Typ.
3. 0°C to +70°C temperature range only.
4. f = 0 means no address or control lines change.
5. At f = f_{MAX}, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/t_{RC}, and using "AC Test Conditions" of input levels of GND to 3V.
6. For the case of one port, divide the appropriate current by four.
7. At $V_{CC} \leq 2.0V$ input leakages are undefined.

DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES

(L Version Only) V_{LC} = 0.2V, V_{HC} = V_{CC} - 0.2V

Symbol	Parameter	Test Condition		Min.	Typ.[1]	Max.	Unit
V_{DR}	Vcc for Data Retention	V_{CC} = 2V		2.0	—	—	V
I_{CCDR}	Data Retention Current	$\overline{CE} \geq V_{HC}$ $V_{IN} \geq V_{HC}$ or $\leq V_{LC}$	MIL.	—	25	1800	µA
			COM'L.	—	25	600	
t_{CDR}[3]	Chip Deselect to Data Retention Time			0	—	—	ns
t_R[3]	Operation Recovery Time			t_{RC}[2]	—	—	ns

2698 tbl 08

NOTES:
1. V_{CC} = 2V, T_A = +25°C
2. t_{RC} = Read Cycle Time
3. This parameter is guaranteed but not tested.

LOW Vcc DATA RETENTION WAVEFORM
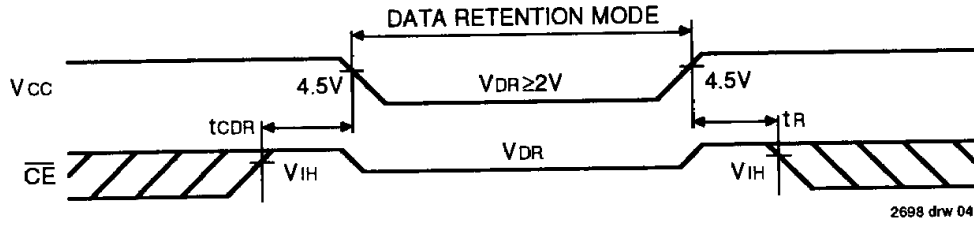
2698 drw 04

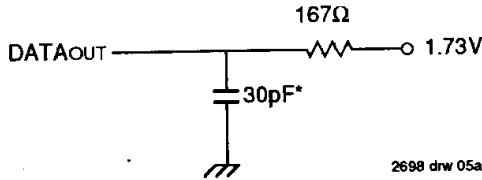## AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1 & 2

2698 tbl 09

2698 drw 05a

*Including scope and jig

Figure 1. Equivalent Output Load
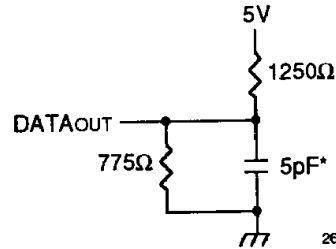
2698 drw 05b

Figure 2. Output Load
(for t_{LZ}, t_{HZ}, t_{WZ}, t_{OW})

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

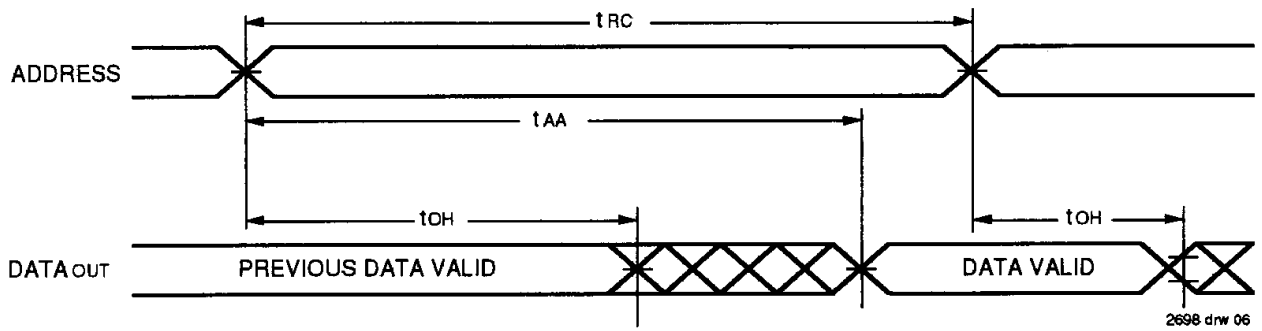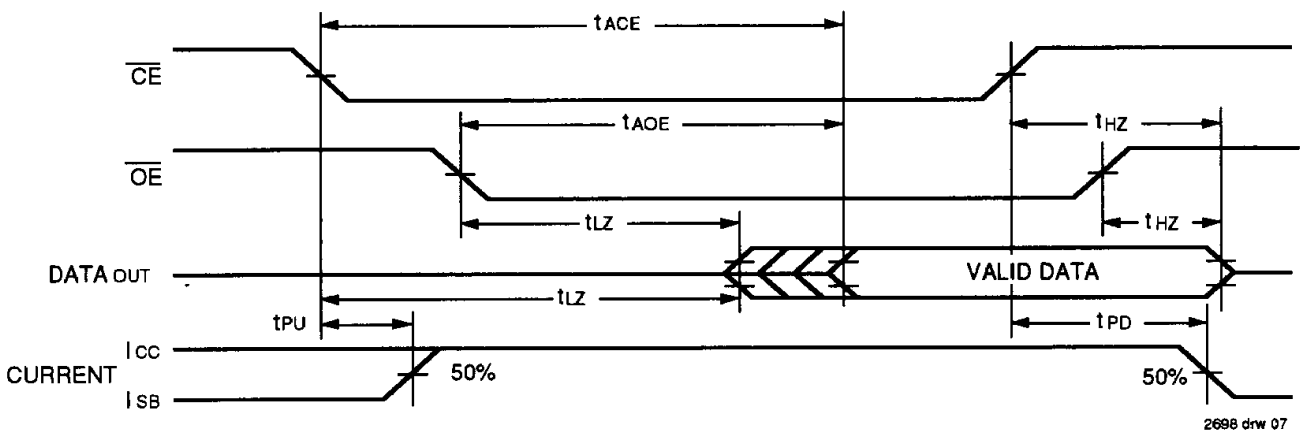| Symbol	Parameter	IDT7050S25[1,3] IDT7050L25[1,3]		IDT7050S30 IDT7050L30		IDT7050S35 IDT7050L35		IDT7050S45 IDT7050L45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t_{RC}	Read Cycle Time	25	—	30	—	35	—	45	—	ns
t_{AA}	Address Access Time	—	25	—	30	—	35	—	45	ns
t_{ACE}	Chip Enable Access Time	—	25	—	30	—	35	—	45	ns
t_{AOE}	Output Enable Access Time	—	15	—	20	—	25	—	30	ns
t_{OH}	Output Hold from Address Change	0	—	0	—	0	—	0	—	ns
t_{LZ}	Output Low Z Time[1,2]	3	—	3	—	5	—	5	—	ns
t_{HZ}	Output High Z Time[1,2]	—	15	—	15	—	15	—	20	ns
t_{PU}	Chip Enable to Power Up Time[2]	0	—	0	—	0	—	0	—	ns
t_{PD}	Chip Disable to Power Down Time[2]	—	20	—	30	—	50	—	50	ns

2698 tbl 10

NOTES:
1. Transition is measured ±500mV from low or high impedance voltage with load (Figures 1 and 2).
2. This parameter is guaranteed but not tested.
3. 0°C to +70°C temperature range only.

6

$\acute{o}-17-6$

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TIMING WAVEFORM OF READ CYCLE NO. 1, ANY PORT[1, 2, 4]

2698 drw 06

TIMING WAVEFORM OF READ CYCLE NO. 2, ANY PORT[1, 3]

2698 drw 07

NOTES:
1. R/W is high for Read Cycles.
2. Device is continuously enabled, $\overline{CE}$ = VIL.
3. Addresses valid prior to or coincident with $\overline{CE}$ transition low.
4. $\overline{OE}$ = VIL.

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AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

| Symbol	Parameter	IDT7050S25[7] IDT7050L25[7] Min.	Max.	IDT7050S30 IDT7050L30 Min.	Max.	IDT7050S35 IDT7050L35 Min.	Max.	IDT7050S45 IDT7050L45 Min.	Max.	Unit
WRITE CYCLE										
t_{WC}	Write Cycle Time	25	—	30	—	35	—	45	—	ns
t_{EW}	Chip Enable to End of Write	20	—	25	—	30	—	35	—	ns
t_{AW}	Address Valid to End of Write	20	—	25	—	30	—	35	—	ns
t_{AS}	Address Set-up Time	0	—	0	—	0	—	0	—	ns
t_{WP}	Write Pulse Width[3]	20	—	25	—	30	—	35	—	ns
t_{WR}	Write Recovery Time	5	—	5	—	5	—	5	—	ns
t_{DW}	Data Valid to End of Write	15	—	15	—	20	—	20	—	ns
t_{HZ}	Output High Z Time[1,2]	—	15	—	15	—	15	—	20	ns
t_{DH}	Data Hold Time	0	—	0	—	0	—	0	—	ns
t_{WZ}	Write Enabled to Output in High Z[1,2]	—	15	—	15	—	15	—	20	ns
t_{OW}	Output Active from End of Write[1,2]	0	—	0	—	0	—	0	—	ns
t_{WDD}	Write Pulse to Data Delay[4]	—	45	—	50	—	55	—	65	ns
t_{DDD}	Write Data Valid to Read Data Delay[4]	—	35	—	40	—	45	—	55	ns
BUSY INPUT TIMING										
t_{WB}	Write to BUSY[5]	0	—	0	—	0	—	0	—	ns
t_{WH}	Write Hold After BUSY[6]	15	—	20	—	20	—	20	—	ns

2698 tbl 11

NOTES:
1. Transition is measured ±500mV from low or high impedance voltage with load (Figures 1 and 2).
2. This parameter is guaranteed but not tested.
3. Specified for OE at high (refer to "Timing Waveform of Write Cycle", Note 7).
4. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Read with Port-to-Port Delay".
5. To ensure that the write cycle is inhibited during contention.
6. To ensure that a write cycle is completed after contention.
7. 0°C to +70°C temperature range only.

6

6-19-8

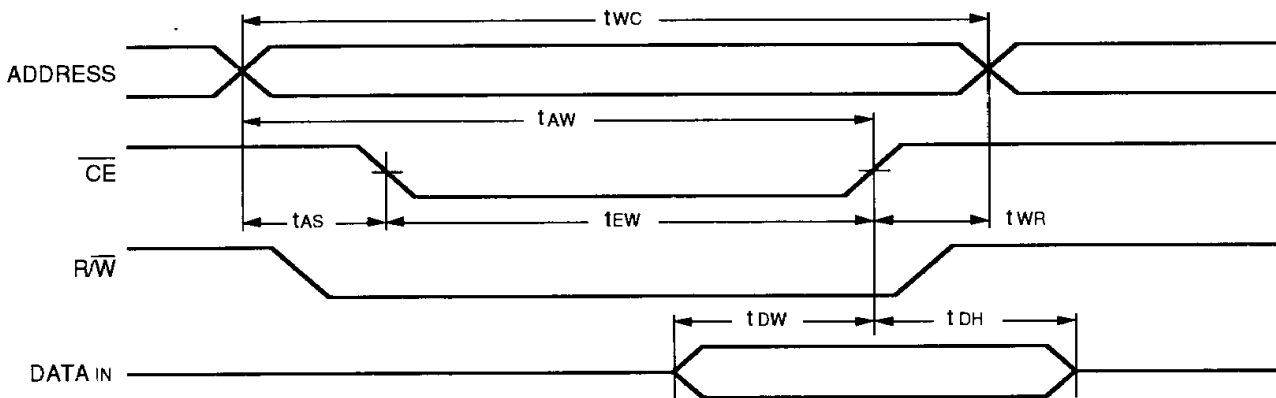## TIMING WAVEFORM OF WRITE CYCLE NO. 1, R/W̄ CONTROLLED TIMING[1, 2, 3, 7]
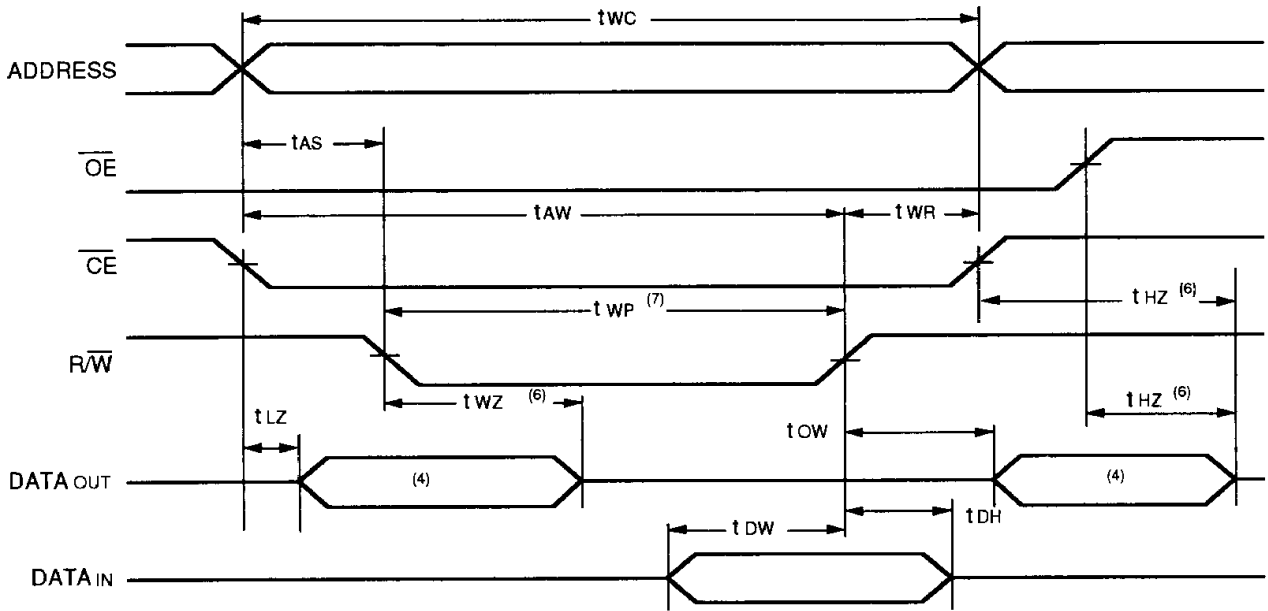
2698 drw 08

## TIMING WAVEFORM OF WRITE CYCLE NO. 2, C̄Ē CONTROLLED TIMING[1, 2, 3, 5]

2698 drw 09

NOTES:
1. R/W̄ or C̄Ē must be high during all address transitions.
2. A write occurs during the overlap (t_EW or t_WP) of a low C̄Ē and a low R/W̄.
3. t_WR is measured from the earlier of C̄Ē or R/W̄ going high to the end of write cycle.
4. During this period, the I/O pins are in the output state, and input signals must not be applied.
5. If the C̄Ē low transition occurs simultaneously with or after the R/W̄ low transition, the outputs remain in the high impedance state.
6. Transition is measured ±500mV from steady state with a 5pF load (including scope and jig). This parameter is sampled and not 100% tested.
7. If O̅Ē is low during a R/W̄ controlled write cycle, the write pulse width must be the larger of t_WP or (t_WZ + t_DW) to allow the I/O drivers to turn off data to be placed on the bus for the required t_DW. If O̅Ē is high during an R/W̄ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_WP.

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TIMING WAVEFORM OF READ WITH PORT-TO-PORT DELAY$^{(1, 2, 3)}$
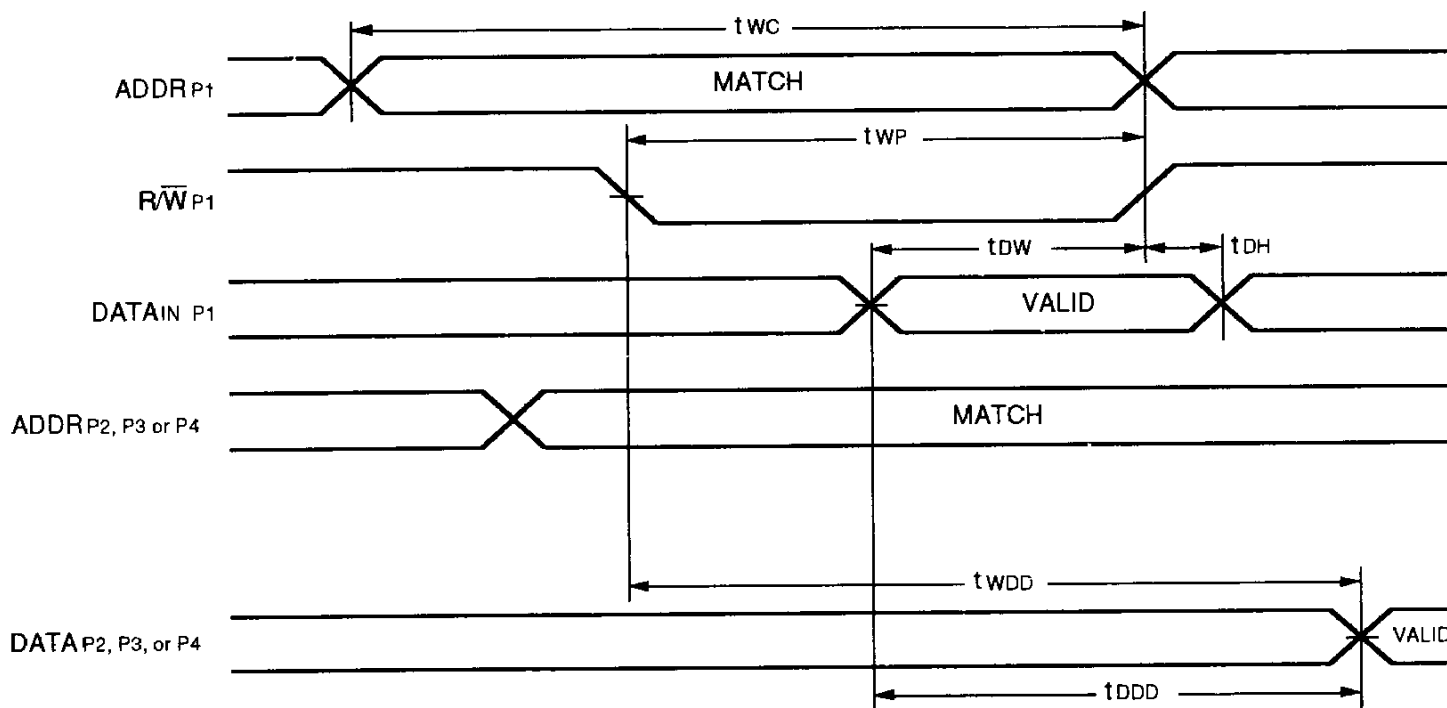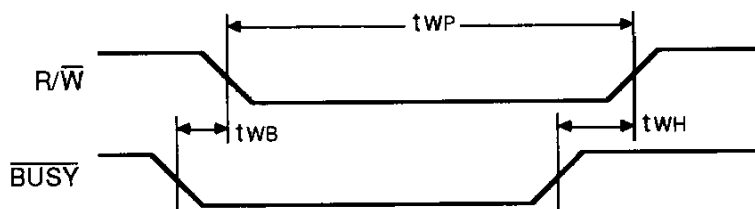

2698 drw 10

NOTES:
1. Assume $\overline{BUSY}$ input at HI and $\overline{CE}$ at LO for the writing port.
2. Write cycle parameters should be adhered to in order to ensure proper writing.
3. Device is continuously enabled for any of the reading ports which has its $\overline{OE}$ at LO.

TIMING WAVEFORM OF WRITE WITH $\overline{BUSY}$ INPUT

2698 drw 11

FUNCTIONAL DESCRIPTION

The IDT7050 provides four ports with separate control, address, and I/O pins that permit independent access for reads or writes to any location in memory. These devices have an automatic power down feature controlled by $\overline{CE}$. The $\overline{CE}$ controls on-chip power down circuitry that permits the respective port to go into standby mode when not selected ($\overline{CE}$ high). When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control ($\overline{OE}$). In the read mode, the port's $\overline{OE}$ turns on the output drivers when set LOW. READ/WRITE conditions are illustrated in the table below.

TABLE I – READ/WRITE CONTROL

Any Port$^{(1)}$				
R/$\overline{W}$	$\overline{CE}$	$\overline{OE}$	D0-7	Function
X	H	X	Z	Port Disabled and in Power Down Mode
X	H	X	Z	$\overline{CE}$P1 = $\overline{CE}$P2 = $\overline{CE}$P3 = $\overline{CE}$P4 = H Power Down Mode, IsB1 or IsB
L	L	X	DATAIN	Data on port written into memory$^{(2, 3)}$
H	L	L	DATAOUT	Data in memory output on port
X	X	H	Z	High impedance outputs

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NOTES:
1. H = HIGH, L = LOW, X = Don't Care, Z = High Impedance
2. If $\overline{BUSY}$ = LOW, data is not written.
3. For valid write operation, no more than one port can write to the same address location at the same time.